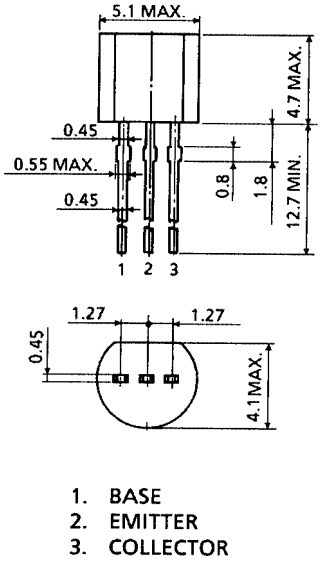
TOSHIBA Transistor Silicon NPN Epitaxial Planar Type

2SC2498

VHF~UHF Band Low Noise Amplifier Application

Unit: mm



JEDEC	TO-92
JEITA	SC-43
TOSHIBA	2-5F1E

Weight: 0.21 g (typ.)

Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	30	V
Collector-emitter voltage	V_{CEO}	20	V
Emitter-base voltage	V_{EBO}	3	V
Collector current	I_C	50	mA
Base current	I_B	25	mA
Collector power dissipation	P_C	300	mW
Junction temperature	T_j	125	°C
Storage temperature range	T_{stg}	−55~125	°C

Microwave Characteristics (Ta = 25°C)

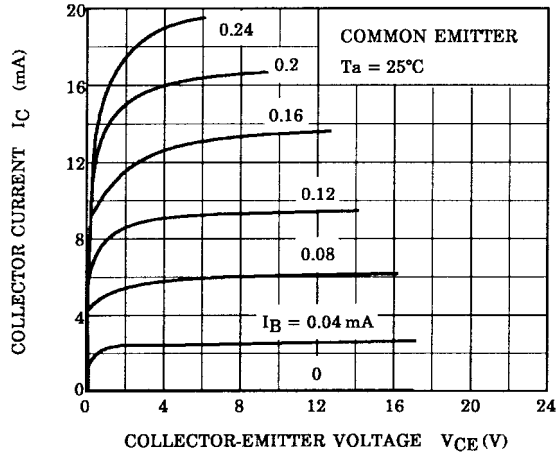
Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Transition frequency	f_T	V_{CE} = 10 V, I_C = 10 mA	—	3.5	—	GHz
Insertion gain	$\|S_{21e}\|^2$ (1)	V_{CE} = 10 V, I_C = 10 mA, f = 500 MHz	—	14.5	—	dB
	$\|S_{21e}\|^2$ (2)	V_{CE} = 10 V, I_C = 10 mA, f = 1 GHz	—	9	—	
Noise figure	NF (1)	V_{CE} = 10 V, I_C = 5 mA, f = 500 MHz	—	2.5	—	dB
	NF (2)	V_{CE} = 10 V, I_C = 5 mA, f = 1 GHz	—	4	—	

Electrical Characteristics (Ta = 25°C)

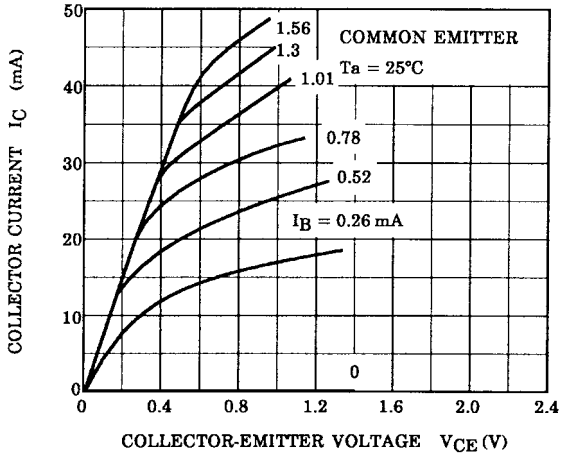
Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current	I_{CBO}	V_{CB} = 10 V, I_E = 0	—	—	1	μA
Emitter cut-off current	I_{EBO}	V_{EB} = 1 V, I_C = 0	—	—	1	μA
DC current gain	h_{FE}	V_{CE} = 10 V, I_C = 10 mA	30	80	300	
Collector output capacitance	C_{ob}	V_{CB} = 10 V, I_E = 0, f = 1 MHz (Note)	—	1.15	—	pF
Reverse transfer capacitance	C_{re}		—	0.75	—	pF

Note: Cre is measured by 3 terminal method with capacitance bridge.

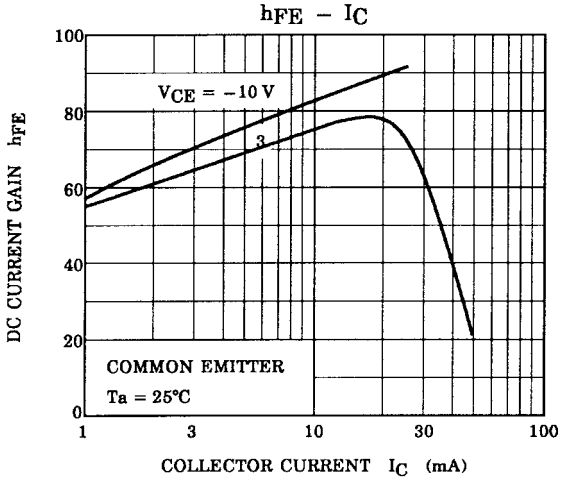
$I_C - V_{CE}$



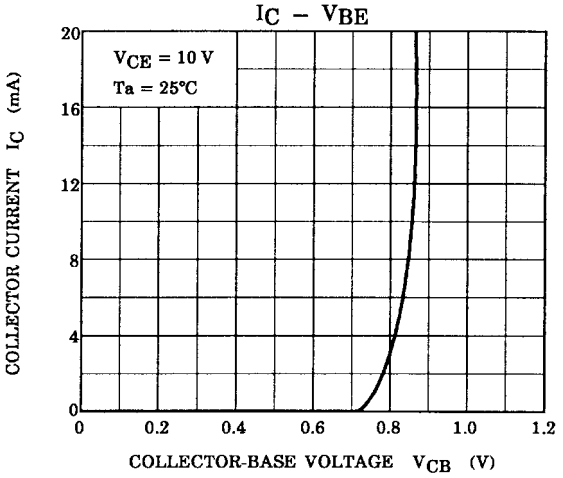
$I_C - V_{CE}$



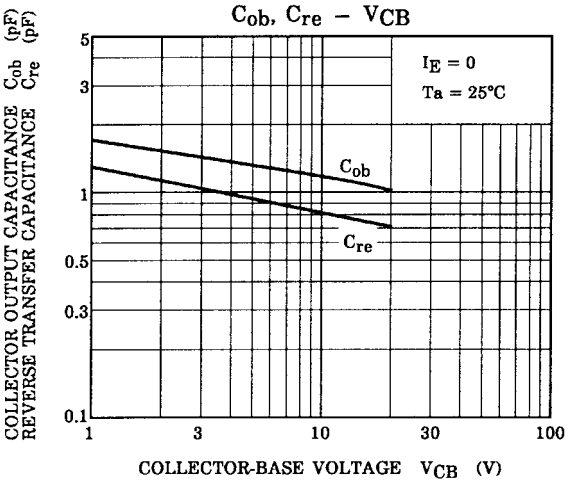
$h_{FE} - I_C$



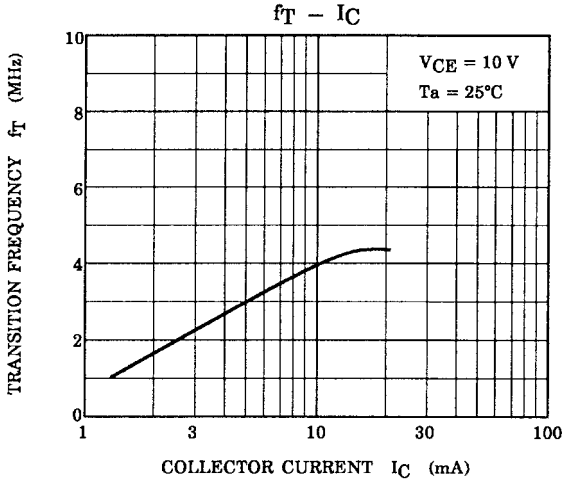
$I_C - V_{BE}$



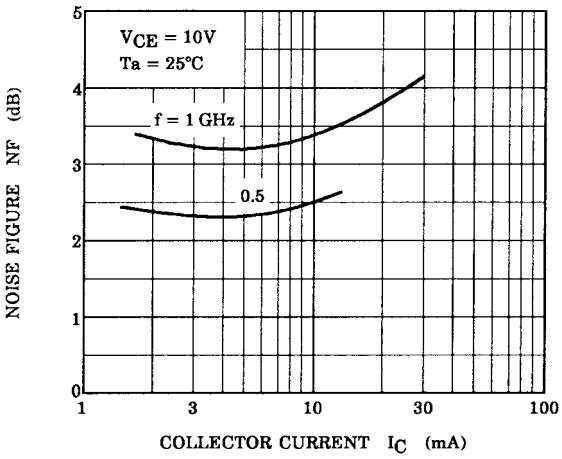
C_{ob}, C_{re} − V_{CB}



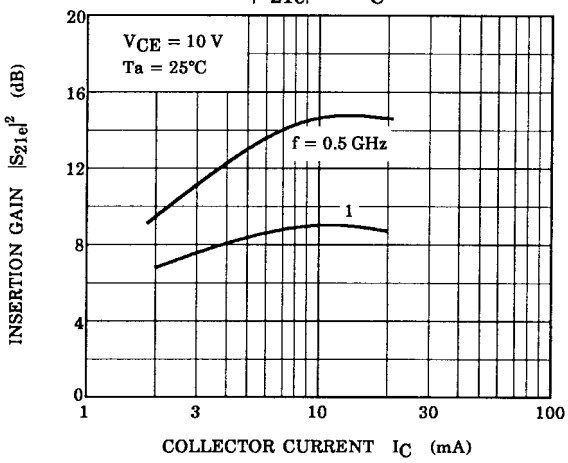
$f_T - I_C$



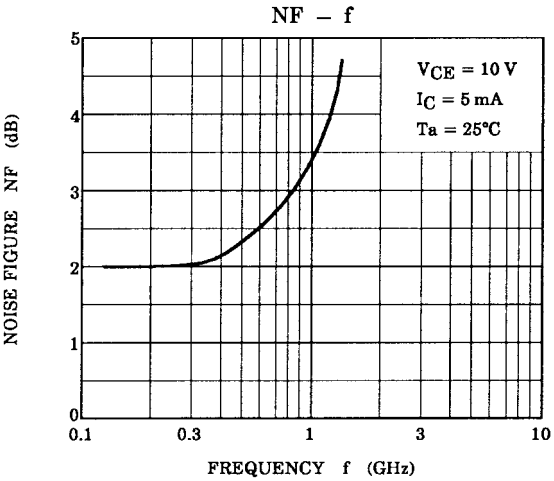
NF – I_C



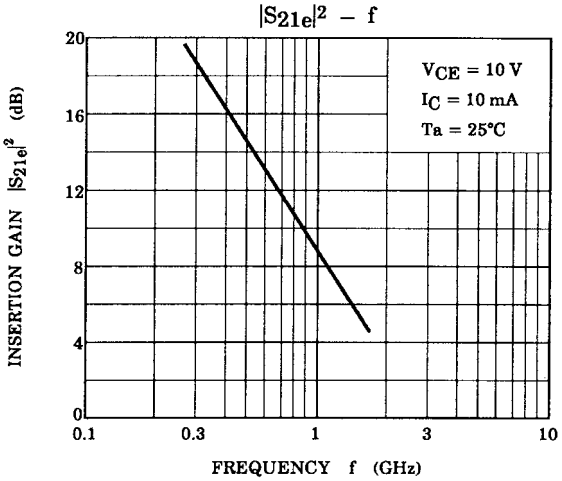
$|S_{21e}|^2$ – I_C



NF – f

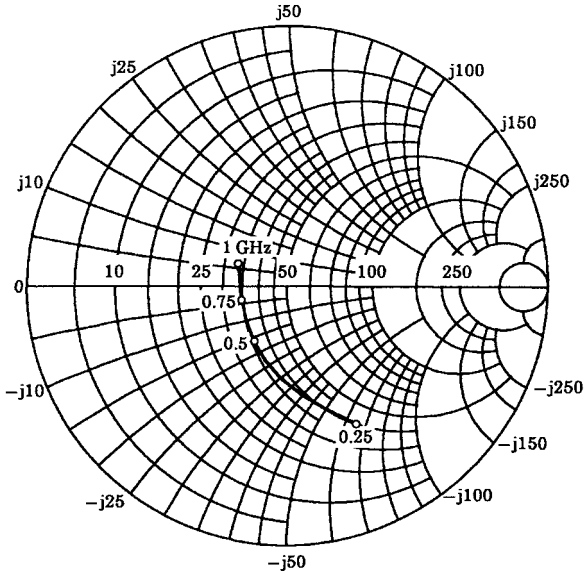


$|S_{21e}|^2$ – f

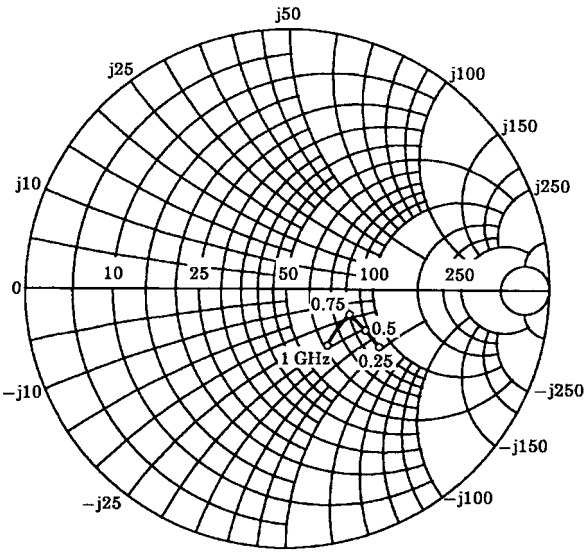


Common Emitter Small Signal S-Parameters of 2SC2498.

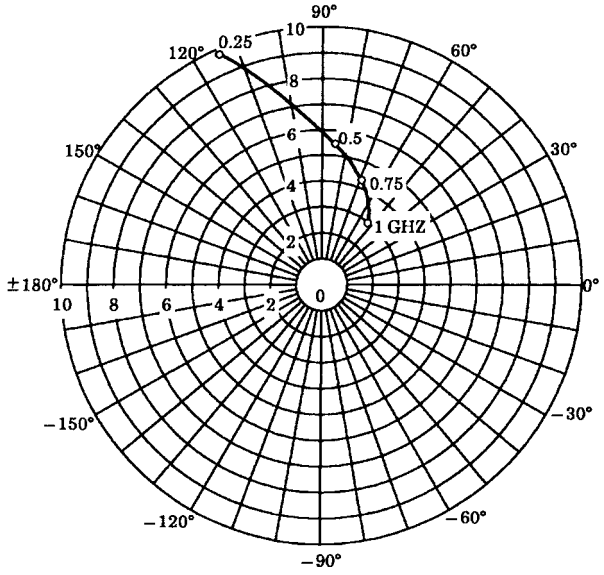
V_{CE} = 10 V, I_C = 10 mA



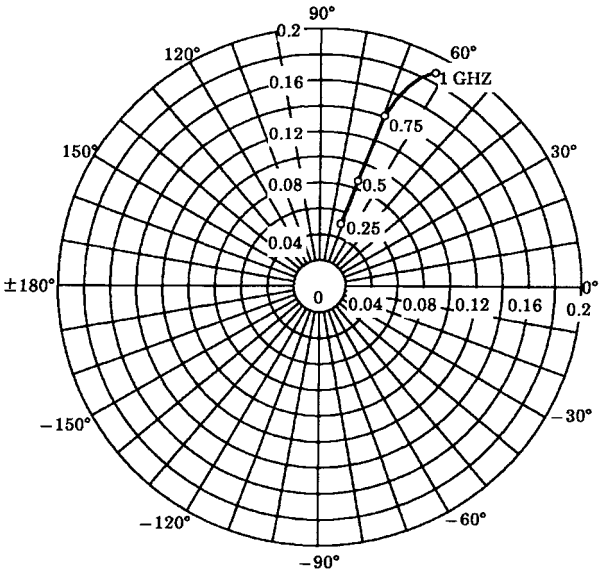
S_{11e} (UNIT : Ω)



S_{22e} (UNIT : Ω)



S_{21e}



S_{12e}

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